SURFACE MOUNT SCHOTTKY BARRIER DIODE

Features

- High breakdown voltage
- Low forward voltage
- Surface mount device

PINNING PIN DESCRIPTION 1 Cathode 2 Anode 1 XH Top View Marking Code: "XH" Simplified outline SOD-123 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

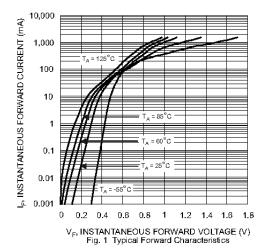
Parameter	Symbol	Value	Unit	
Repetitive Peak Reverse Voltage	V_{RRM}	100	V	
Continuous Forward Current	I _F	150	mA	
Repetitive Peak Forward Current (at tp < 1 s)	I _{FRM}	350	mA	
Surge Forward Current (at tp < 10 ms)	I _{FSM}	750	mA	
Power Dissipation	P _{tot}	200	mW	
Thermal Resistance Junction Ambient	R _{thJA}	420	°C/W	
Operating Temperature Range	TJ	- 55 to + 125	°C	
Storage Temperature Range	T _s	- 55 to + 150	°C	

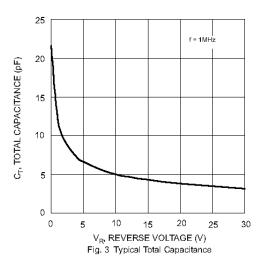
Characteristics at T_a = 25 °C

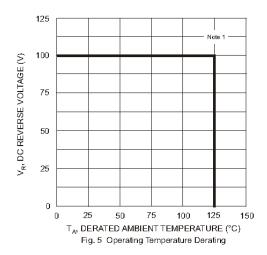
Parameter	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu A$	$V_{(BR)R}$	100	ı	-	V
Forward Voltage at $I_F = 0.1$ mA at $I_F = 10$ mA at $I_F = 250$ mA	V _F		- - -	0.25 0.45 1	V
Reverse Current at $V_R = 1.5 \text{ V}$ at $V_R = 10 \text{ V}$ at $V_R = 50 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 1.5 \text{ V}$, $T_j = 60 ^{\circ}\text{C}$ at $V_R = 10 \text{ V}$, $T_j = 60 ^{\circ}\text{C}$ at $V_R = 50 \text{ V}$, $T_j = 60 ^{\circ}\text{C}$ at $V_R = 75 \text{ V}$, $T_j = 60 ^{\circ}\text{C}$	I R		- - - - -	0.5 0.8 2 5 5 7.5 15	μА
Total Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$	Ст		20 12	- -	pF

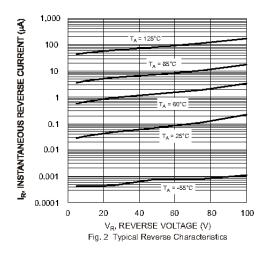


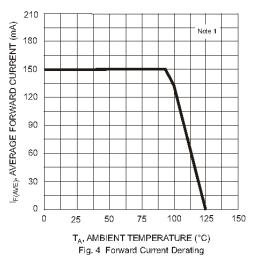












Note 1: Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



SEMTECH ELECTRONICS LTD.







Dated : 06/07/2007

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123

